

Silicon NPN Power Transistors

3DD207

DESCRIPTION

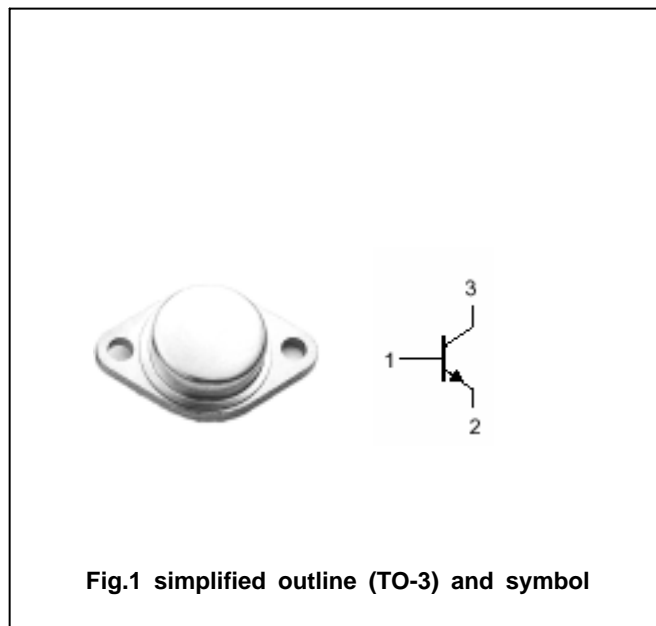
- With TO-3 package
- Low collector saturation voltage

APPLICATIONS

- For audio amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
P _C	Collector power dissipation	T _C =75	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

 $T_j=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3A ; I_B=0.3A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=3A ; I_B=0.3A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=60V ; I_E=0$			0.5	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=2A ; V_{CE}=5V$	40		250	

PACKAGE OUTLINE

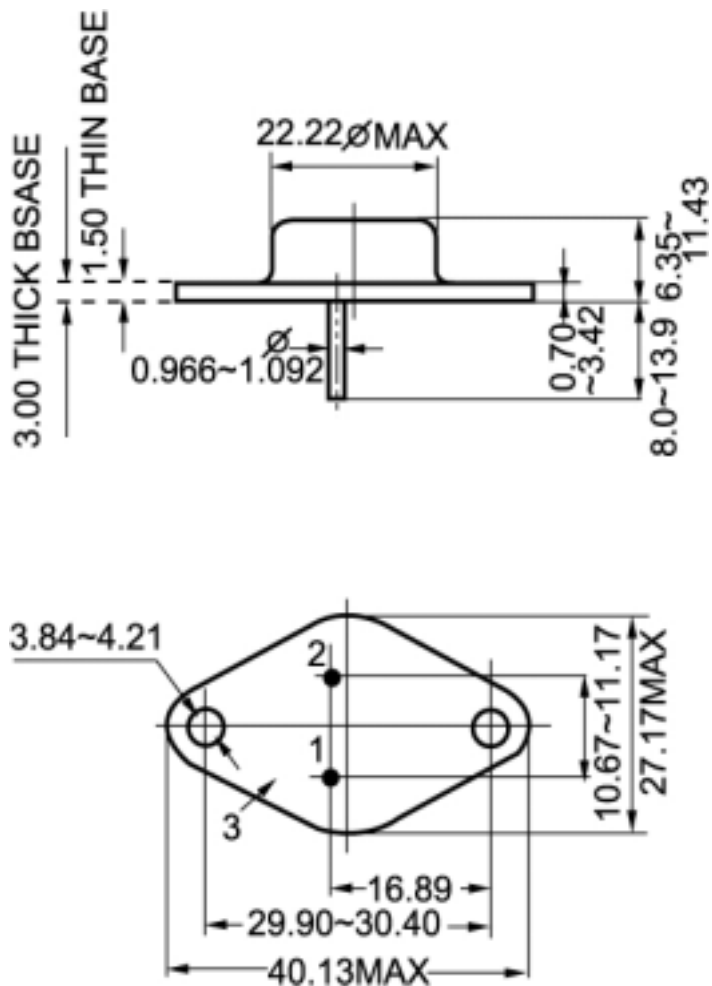


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)